

Substitute Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 10559-586003	Application No.
<b>Information Disclosure Statement</b> <b>by Applicant</b> <small>(Use several sheets if necessary)</small> <small>(37 CFR §1.98(b))</small>		Applicant Lawrence D. Wong		
		Filing Date March 16, 2004	Group Art Unit	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	4,848,141	07/1989	Oliver et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation
							Yes No
	AH						
	AI						
	AJ						

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	AK	P.T. Liu et al., Thin Solid Films 332 (1998) 345-350.
	AL	E. Kondoh, Electrochemical and Solid-State Letters, 1, (5) 224-226 (1998).
	AM	Gidley et. al., Applied Physics Letters, 76 (2000) p. 1282
	AN	Loboda et. al., Using trimethylsilane to improve safety, throughput and versatility in PECVD processes, Proceedings of the Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, 1997, p. 445-453.
	AO	Loboda et. al., Deposition of low-k dielectric films using trimethylsilane, Proceedings of the Symposia on Electrochemical Processing in ULSI Fabrication and Interconnect and Contact Metallization: Materials, Processes, and Reliability, 1998, p. 145-152.
	AP	Sugahara et. al., Low Dielectric Constant Carbon Containing SiO <sub>2</sub> Films Deposited by PECVD Techniques Using a Novel CVD Precursor, International dielectrics for ULSI multilevel interconnection conference, 1997, p. 19-25.
	AQ	Kanaya K. and Okayama S., Journal of Physics D. Applied Physics. 5:43 (1972).
	AR	

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

**Notice of References Cited**

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Application/Control No.  
10559-586003  
March 16, 2004Applicant(s)/Patent Under  
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
A	US-6,340,628 B1		01-2002	Van Cleemput et al.	438/586
B	US-				
C	US-				
D	US-				
E	US-				
F	US-				
G	US-				
H	US-				
I	US-				
J	US-				
K	US-				
L	US-				
M	US-				

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
N						
O						
P						
Q						
R						
S						
T						

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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	V	
	W	
	X	

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Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

<b>Notice of References Cited</b>	Filed:	Application/Control No. 10559-586003 March 16, 2004	Applicant(s)/Patent Under Reexamination
		Examiner	Art Unit Page 1 of 1

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**NON-PATENT DOCUMENTS**

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	U	Hara et al., "Mechanism of mechanical and chemical polishing in low dielectric constant plasma-enhanced chemical vapor deposition SiOC layer from hexamethydisiloxane", Aug. 2001, Electrochem. and Solid-State Lett., vol. 4, no. 8, P. G65-67.
	V	Music et al., "Synthesis and mechanical properties of boron suboxide thin films", Apr 2002, J. Vac. Sci. Technol. A 20(2), p.335-337.
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	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.